Abstracts

Si/SiGe MMIC Technology

J.-F. Luy, K.M. Strohm and E. Sasse. "Si/SiGe MMIC Technology." 1994 MTT-S International Microwave Symposium Digest 94.3 (1994 Vol. III [MWSYM]): 1755-1757.

This contribution gives an overview on the state of the art of Si/SiGe MMIC technology. IMPATT Diodes for transmitters, Schottky diodes for mixers and PIN diodes for switches at W-band frequencies and SiGe-HBTs for oscillators at Ka-band frequencies are integrated on high resistivity silicon substrate.

☐ Return to main document.

Click on title for a complete paper.